XBS024S15R-G



ETR1605-003

Schottky Barrier Diode, 200mA, 40V Type

■FEATURES

: V_F=0.53V (TYP.) Forward Voltage

Forward Current : I_{F(AV)}=200mA Repetitive Peak Reverse Voltage: V_{RM}=40V

: EU RoHS Compliant, Pb Free Environmentally Friendly

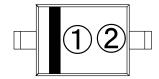
■ ABSOLUTE MAXIMUM RATINGS

Tم.	_21	5°C

PARMETER	SYMBOL	RATINGS	UNIT	
Repetitive Peak Voltage	VRM	40	V	
Reverse Voltage (DC)	VR	40	V	
Forward Current (Average)	lF(AV)	200	mA	
Non Continuous	IFSM	1	۸	
Forward Surge Current ^{*1}	IF5M	ı	А	
Junction Temperature	Tj	125	လူ	
Storage Temperature Range	Tstg	-55 ~ +150	°C	
Storage Temperature Range	istg	-55~+150	·C	

^{*1 :} Non continuous high amplitude 60Hz half-sine wave.

■MARKING RULE

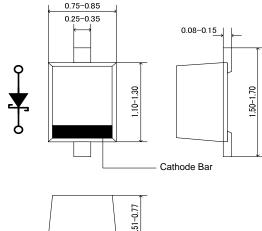


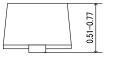
- 1: 1 (Product Number)
- 2: Assembly Lot Number

■APPLICATIONS

■Low Current Rectification

■ PACKAGING INFORMATION





SOD-523

Unit: mm

■PRODUCT NAME

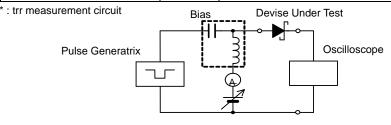
PRODUCT NAME	DEVICE ORIENTATION		
XBS024S15R	SOD-523		
XBS024S15R-G	SOD-523(Halogen & Antimony free)		

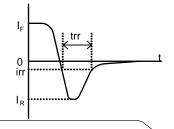
^{*} The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

■ELECTRICAL CHARACTERISTICS

Ta=25°C

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN.	TYP.	MAX.	UNIT
Forward Voltage	VF1	I _F =10mA	-	0.33	-	V
	VF2	I _F =200mA	-	0.53	0.6	V
Reverse Current	lr	V _R =40V	-	-	2	μΑ
Inter-Terminal Capacity	Ct	V _R =10V , f=1MHz	-	5	-	pF
Reverse Recovery Time*	trr	I _F =I _R =10mA , irr=1mA	-	4	-	ns

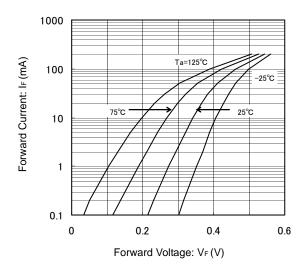




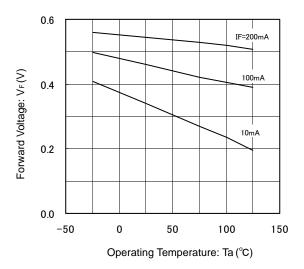
^{*} The device orientation is fixed in its embossed tape pocket.

■TYPICAL PERFORMANCE CHARACTERISTICS

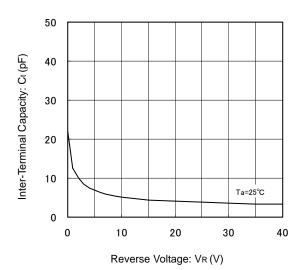
(1) Forward Current vs. Forward Voltage



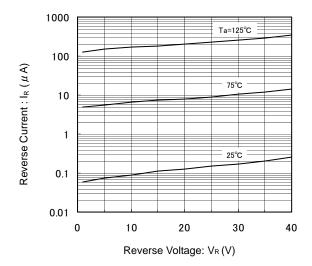
(3) Forward Voltage vs. Operating Temperature



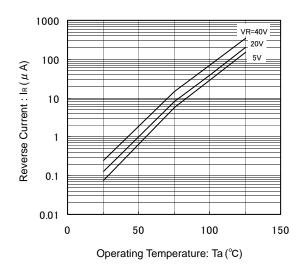
(5) Inter-Terminal Capacity vs. Reverse Voltage



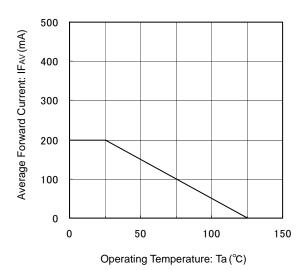
(2) Reverse Current vs. Reverse Voltage



(4) Reverse Current vs. Operating Temperature



(6) Average Forward Current vs. Operating Temperature



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